## **Plastic Infrared Emitting Diode**

## OP265WPS



#### Features:

- T-1 (3 mm) package style
- Broad irradiance pattern
- Point source with flat lens
- Higher power output than GaAs at equivalent drive currents
- 850 nm diode

#### **Description:**

The **OP265WPS** *point source* model is a flat-lensed 850 nm diode with a *broad* radiation pattern that provides relatively even illumination over a large area. Its stable forward voltage ( $V_F$ ) vs. temperature characteristic makes this device appropriate for applications where voltage is limited (such as battery operation), while the low rise time/fall time ( $t_r/t_f$ ) makes it ideal for high-speed operation.

OP265 devices conform to the OP505 and OP535 series devices.

Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.

LED Peak

Wavelength

850 nm

Part

Number

OP265WPS

#### **Applications:**

- Space-limited applications
- Applications requiring coupling efficiency
- Precision optical designs
- Battery-operated or voltage-limited applications



**Ordering Information** 

I<sub>F</sub> (mA)

Typ / Max

20 / 50

**Total Beam** 

Angle

120°

Lead

Length

0.50"

Output Power (mW/cm<sup>2</sup>)

Min / Max

.055 / .55

General Note

RoHS

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

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## **Electrical Specifications**

Absolute Maximum Ratings (T <sub>A</sub> = 25° C unless otherwise noted)				
Storage and Operating Temperature Range	-40° C to +100° C			
Reverse Voltage	2.0 V			
Continuous Forward Current	50 mA			
Peak Forward Current (1 μs pulse width, 300 pps)	3.0 A			
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C <sup>(1)</sup>			
Power Dissipation	100 mW <sup>(2)</sup>			

Notes:

- 1. RMA flux is recommended. Duration can be extended to 10 second maximum when flow soldering. A maximum of 20 grams force may be applied to the leads when soldering.
- 2. Derate linearly at 1.33 mW/° C above 25° C.
- E<sub>E(APT)</sub> is a measurement of the average apertured radiant incidence upon a sensing area 0.081" (2.06 mm) in diameter, perpendicular to and centered on the mechanical axis of the lens and 0.590" (14.99 mm) from the measurement surface. E<sub>E(APT)</sub> is not necessarily uniform within the measured area.

Electrical Characteristics (T <sub>A</sub> = 25° C unless otherwise noted)							
SYMBOL	PARAMETER	MIN	ТҮР	MAX	UNITS	TEST CONDITIONS	
Input Diode							
Е <sub>Е (АРТ)</sub>	Apertured Radiant Incidence	2.70	-	-	mW/cm <sup>2</sup>	$I_{\rm F} = 20 \ {\rm mA}^{(3)}$	
V <sub>F</sub>	Forward Voltage	-	-	1.80	V	I <sub>F</sub> = 20 mA	
I <sub>R</sub>	Reverse Current	-	-	20	μA	V <sub>R</sub> = 2 V	
$\lambda_{P}$	Wavelength at Peak Emission	-	850	-	nm	I <sub>F</sub> = 10 mA	
В	Spectral Bandwidth between Half Power Points	-	-	-	nm	I <sub>F</sub> = 20 mA	

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### Performance OP265WPS







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